

GENERAL PURPOSE SWITCHING AND AMPLIFIER TRANSISTORS (SILICON)

Current versus Voltage

BV _{CEO} Min Volts	OPTIMUM COLLECTOR CURRENT									
	0 to 10 mA		10 mA to 100 mA		100 mA to 500 mA		500 mA to 1.0 A		1.0 A to 3.0 A	
	NPN	PNP	NPN	PNP	NPN	PNP	NPN	PNP	NPN	PNP
15 ↓ 29	2N916 2N2330 2N2331		2N916 2N1983 2N1984		2N696 2N697 2N718 2N1420 2N2195	2N1991				
30 ↓ 39			2N2218 2N2219 2N2221 2N2222	2N3133 2N3134 2N3135 2N3136	2N2218 2N2219 2N2221 2N2222 2N3299 2N3300 2N3301 2N3302	2N2800 2N2801 2N2837 2N2838 2N3133 2N3134 2N3135 2N3136				
49 ↓ 59	2N758 2N795 2N760 2N915 2N929 2N930 2N3946 2N3947	2N3250 2N3251 MM4048	2N2218A 2N2219A 2N2221A 2N2222A 2N2224 2N3946 2N3947	2N3250 2N3251	2N2194 2N2218A 2N2219A 2N2221A 2N2222A	2N2904 2N2905 2N2906 2N2907 2N3485 2N3486 2N4890	2N32192 2N32193	2N3244 2N3245	2N3506 2N3507	
60 ↓ 79	2N758A 2N759A 2N760A 2N929A 2N930A MM2483 MM2484	2N3798 2N3799 2N3250A 2N3251A	2N910 2N911 2N1990	2N3250A 2N3251A	2N656 2N699	2N2904A 2N2905A 2N2906A 2N2907A 2N3485A 2N3486A				
80 ↓ 99	2N739 2N740	2N3494 2N3496	2N720A 2N1893 2N2405	2N3494 2N3496	2N720A 2N3019 2N3020		2N3019 2N3020			
100 ↓ 149	2N4924	2N3495 2N3497 2N4928	2N3498 2N3499 2N4924	2N3495 2N3497 2N3634 2N3635 2N4928	2N3498 2N3499 2N4924	2N3634 2N3635				
150 ↓ 249	2N3114 2N4925 2N4926	2N4929 2N4930	2N3500 2N3501 2N4925 2N4926	2N3635 2N3637 2N4929 2N4930	2N3500 2N3501 2N4925	2N3636 2N3637				
250 UP	2N3742 2N4927	2N3743 2N4931	2N3742 2N4927	2N3743 2N4931						

2N3724, 2N3725 — 2N4013, 2N4014 (continued)

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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ON CHARACTERISTICS (continued)

Collector-Emitter Saturation Voltage* ($I_C = 10\text{ mAdc}$, $I_B = 1.0\text{ mAdc}$)	2N3724, 2N4013 2N3725, 2N4014 2N3724, 2N4013 2N3725, 2N4014 2N3724, 2N4013 2N3725, 2N4014 2N3724, 2N4013 2N3725, 2N4014	$V_{CE(sat)}^*$	-	0.25	Vdc
($I_C = 100\text{ mAdc}$, $I_B = 10\text{ mAdc}$)			-	0.20	
($I_C = 300\text{ mAdc}$, $I_B = 30\text{ mAdc}$)			-	0.26	
($I_C = 500\text{ mAdc}$, $I_B = 50\text{ mAdc}$)			-	0.32	
($I_C = 800\text{ mAdc}$, $I_B = 80\text{ mAdc}$)			-	0.40	
($I_C = 1.0\text{ Adc}$, $I_B = 100\text{ mAdc}$)			-	0.42	
($I_C = 1.0\text{ Adc}$, $I_B = 100\text{ mAdc}$)			-	0.52	
Base-Emitter Saturation Voltage* ($I_C = 10\text{ mAdc}$, $I_B = 1.0\text{ mAdc}$)	2N3724, 2N4013 2N3725, 2N4014 2N3724, 2N4013 2N3725, 2N4014 2N3724, 2N4013 2N3725, 2N4014 2N3724, 2N4013 2N3725, 2N4014	$V_{BE(sat)}^*$	-	0.76	Vdc
($I_C = 100\text{ mAdc}$, $I_B = 10\text{ mAdc}$)			-	0.86	
($I_C = 300\text{ mAdc}$, $I_B = 30\text{ mAdc}$)			-	1.1	
($I_C = 500\text{ mAdc}$, $I_B = 50\text{ mAdc}$)			0.9	1.2	
($I_C = 800\text{ mAdc}$, $I_B = 80\text{ mAdc}$)			-	1.5	
($I_C = 1.0\text{ Adc}$, $I_B = 100\text{ mAdc}$)			-	1.7	
($I_C = 1.0\text{ Adc}$, $I_B = 100\text{ mAdc}$)			-	0.95	

SMALL-SIGNAL CHARACTERISTICS

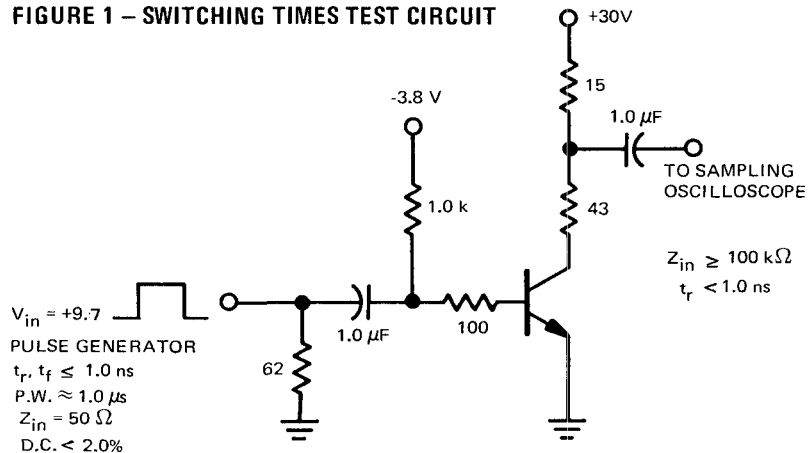
Current-Gain-Bandwidth Product ($I_C = 50\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	300	-	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 140\text{ kHz}$)	C_{ob}	-	12	pF
		-	10	
Input Capacitance ($V_{BE} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 140\text{ kHz}$)	C_{ib}	-	55	pF

SWITCHING CHARACTERISTICS

Turn-On Time	$(V_{CC} = 30\text{ Vdc}$, $V_{BE(off)} = 3.8\text{ Vdc}$, $I_C = 500\text{ mAdc}$, $I_{B1} = 50\text{ mAdc}$) (See Figure 1)	t_{on}	-	35	ns
Delay Time		t_d	-	10	ns
Rise Time		t_r	-	30	ns
Turn-Off Time	$(V_{CC} = 30\text{ Vdc}$, $I_C = 500\text{ mAdc}$, $I_{B1} = I_{B2} = 50\text{ mAdc}$) (See Figure 1)	t_{off}	-	60	ns
Storage Time		t_s	-	50	ns
Fall Time		t_f	-	25	ns
				30	ns

* Pulse Test: Pulse Width = 300 μs , Duty Cycle = 1.0%.

FIGURE 1 — SWITCHING TIMES TEST CIRCUIT



2N3743 (SILICON)

$V_{CEO} = 300\text{ V}$
 $I_C = 50\text{ mA}$



PNP silicon annular transistor for high-voltage amplifier applications from dc to VHF.

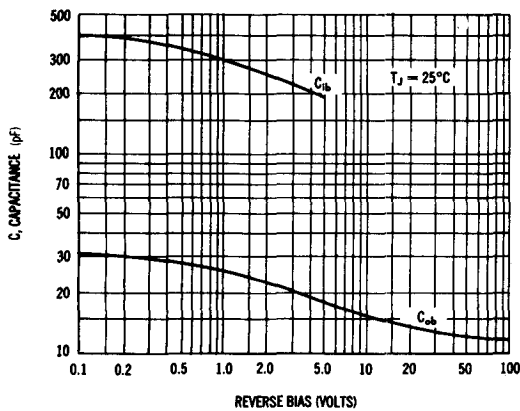
Collector connected to case

CASE 31
(TO-5)

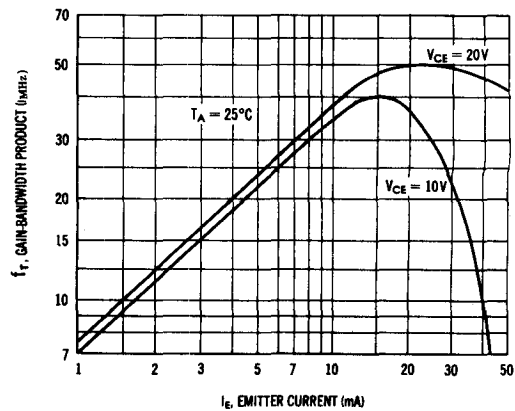
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Base Voltage	V_{CB}	300	Vdc
Collector-Emitter Voltage	V_{CEO}	300	Vdc
Emitter-Base Voltage	V_{EB}	5	Vdc
Collector Current	I_C	50	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$	P_D	1.0	Watt
Derate Above 25°C		5.7	mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$	P_D	5.0	Watts
Derate Above 25°C		28.6	mW/ $^\circ\text{C}$
Operating Junction Temperature	T_J	+200	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +200	$^\circ\text{C}$

JUNCTION CAPACITANCE



GAIN-BANDWIDTH PRODUCT



2N3743 (continued)

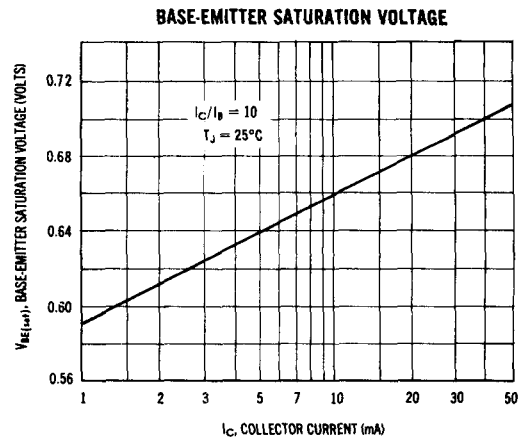
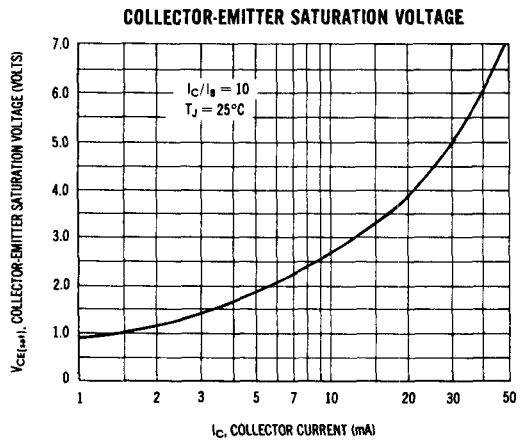
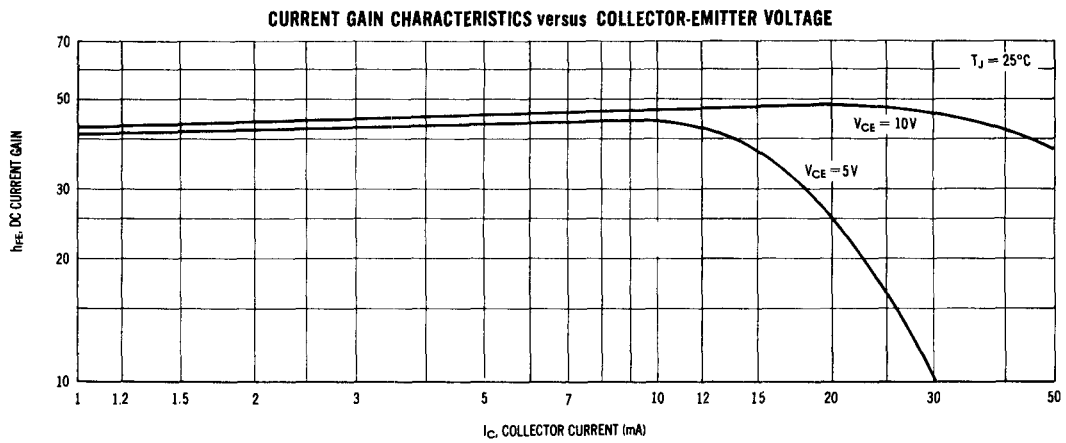
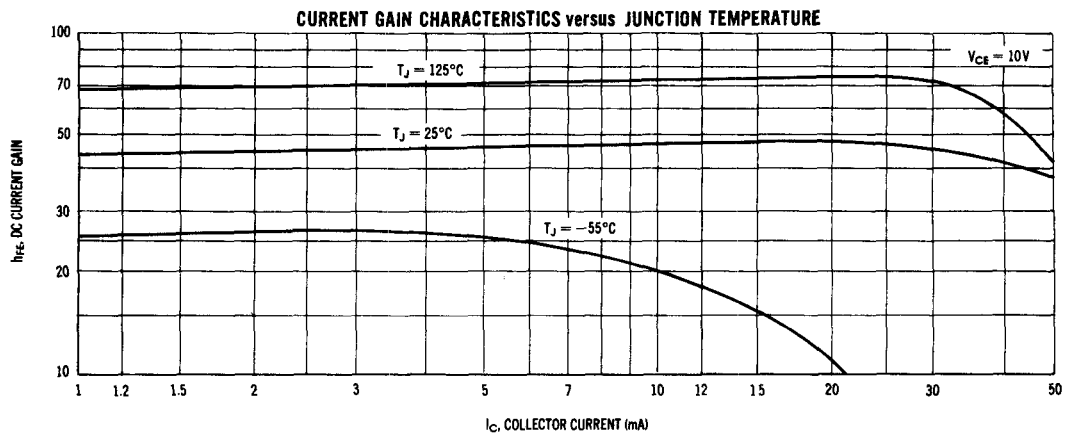
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Min	Max	Unit
Collector-Base Breakdown Voltage ($I_C = 100 \mu\text{Adc}$, $I_E = 0$)	BV_{CBO}	300	—	Vdc
Collector-Emitter Breakdown Voltage* ($I_C = 10 \text{ mAdc}$, $I_B = 0$)	BV_{CEO}^*	300	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100 \mu\text{Adc}$, $I_C = 0$)	BV_{EBO}	5	—	Vdc
Collector Saturation Voltage** ($I_C = 10 \text{ mAdc}$, $I_B = 1 \text{ mAdc}$) ($I_C = 30 \text{ mAdc}$, $I_B = 3 \text{ mAdc}$)	$V_{CE(sat)}^{**}$	— —	5 8	Vdc
Base-Emitter Saturation Voltage** ($I_C = 10 \text{ mAdc}$, $I_B = 1 \text{ mAdc}$) ($I_C = 30 \text{ mAdc}$, $I_B = 3 \text{ mAdc}$)	$V_{BE(sat)}^{**}$	— —	1.0 1.2	Vdc
DC Forward Current Gain** ($I_C = 100 \mu\text{Adc}$, $V_{CE} = 10 \text{ Vdc}$) ($I_C = 1 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$) ($I_C = 30 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$) ($I_C = 50 \text{ mAdc}$, $V_{CE} = 20 \text{ Vdc}$)	h_{FE}^{**}	20 25 25 25 25	— — — 250 —	—
Collector Cutoff Current ($V_{CB} = 200 \text{ Vdc}$, $I_E = 0$) ($V_{CB} = 200 \text{ Vdc}$, $I_E = 0$, $T_A = 100^\circ\text{C}$)	I_{CBO}	— —	0.3 30	μAdc
Emitter-Base Leakage Current ($V_{EB} = 3 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	0.1	μAdc
Small-Signal Current Gain ($I_C = 10 \text{ mAdc}$, $V_{CE} = 20 \text{ Vdc}$, $t = 20 \text{ MHz}$)	$ h_{fe} $	1.5	—	—
Output Capacitance ($V_{CB} = 20 \text{ Vdc}$, $I_E = 0$, $f = 100 \text{ kHz}$)	C_{ob}	—	15	pF
Input Capacitance ($V_{EB} = 1 \text{ Vdc}$, $I_C = 0$, $f = 100 \text{ kHz}$)	C_{ib}	—	400	pF
Small Signal Current Gain ($V_{CE} = 10 \text{ V}$, $I_C = 10 \text{ mA}$, $f = 1 \text{ kHz}$)	h_{fe}	30	300	—
Voltage Feedback Ratio ($V_{CE} = 10 \text{ V}$, $I_C = 10 \text{ mA}$, $f = 1 \text{ kHz}$)	h_{re}	—	4.0	$\times 10^{-4}$
Input Impedance ($V_{CE} = 10 \text{ V}$, $I_C = 10 \text{ mA}$, $f = 1 \text{ kHz}$)	h_{ie}	—	1.0	kohms
Output Admittance ($V_{CE} = 10 \text{ V}$, $I_C = 10 \text{ mA}$, $f = 1 \text{ kHz}$)	h_{oe}	—	200	μmhos
Real Part of Input Impedance ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 5 \text{ MHz}$)	$\text{Re}(h_{ie})$	—	40	ohms

*PW $\leq 30 \mu\text{s}$, Duty Cycle $\leq 1\%$

**PW $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$

2N3743 (continued)



2N3743 (continued)

SMALL SIGNAL Y PARAMETERS

$T_A = 25^\circ\text{C}$

